

YJ Planar Schottky Barrier Diode Die Specification

100V 1A, 32mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB032H100SS-280A

Main Products Characteristics

- Average forward current: $I_F(AV) = 1 \text{ A}$
- Maximum operating junction temperature: $T_j = 175 \text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

$I_F = 1 \text{ A}$

Pulse Test: $t_p = 300 \mu\text{s}$, 2%

Device Schematics and Outline Drawing

Die Thickness *

Die Size **